TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74LCX16240FT

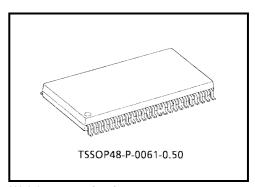
Low-Voltage 16-Bit Bus Buffer (inverted) with 5-V Tolerant Inputs and Outputs

The TC74LCX16240FT is a high-performance CMOS 16-bit bus buffer. Designed for use in 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

The device is designed for low-voltage (2.5-V or 3.3-V) VCC applications, but it could be used to interface to 5-V supply environment for both inputs and outputs.

This device is inverting 3-state buffer having four active-low output enables. It can be used as four 4-bit buffers two 8-bit buffers or one 16-bit buffer. When the $\overline{\rm OE}$ input is high, the outputs are in a high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge.



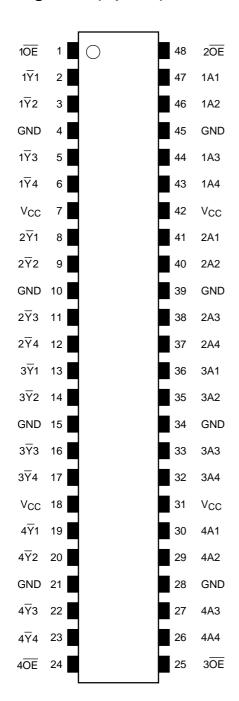
Weight: 0.25 g (typ.)

Features

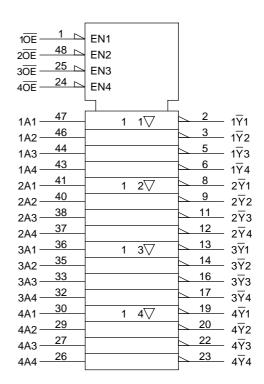
- Low-voltage operation: $V_{CC} = 2.0$ to 3.6 V
- High-speed operation: $t_{pd} = 4.5 \text{ ns (max) (VCC} = 3.0 \text{ to } 3.6 \text{ V)}$
- Output current: $|I_{OH}|/I_{OL} = 24 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$
- Latch-up performance: ±500 mA
- Package: TSSOP (thin shrink small outline package)
- Power-down protection provided on all inputs and outputs

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Pin Assignment (top view)



IEC Logic Symbol



Truth Table

Inp	Outputs	
1 OE	1A1-1A4	1 <u>7</u> 1 - 1 <u>7</u> 4
L	L	Н
L	Н	L
Н	X	Z

Inp	Outputs	
2 OE	2A1-2A4	2 <u>Y</u> 1 - 2 <u>Y</u> 4
L	L	Н
L	Н	L
Н	Х	Z

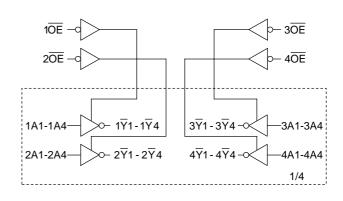
Inp	Outputs	
3 OE	3A1-3A4	3 <u>Y</u> 1 - 3 <u>Y</u> 4
L	L	Н
L	Н	L
Н	Х	Z

Inp	Outputs	
4 OE	4A1-4A4	4 <u>Y</u> 1 - 4 <u>Y</u> 4
L	L	Н
L	Н	L
Н	Х	Z

X: Don't care

Z: High impedance

System Diagram





Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5 to 6.0	V
Input voltage	V _{IN}	-0.5 to 7.0	V
Output voltage	V	-0.5 to 7.0 (Note 1)	V
Output Voltage	V _{OUT}	-0.5 to V _{CC} + 0.5 (Note 2)	V
Input diode current	I _{IK}	-50	mA
Output diode current	lok	±50 (Note 3)	mA
DC output current	I _{OUT}	±50	mA
Power dissipation	P_{D}	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Output in OFF state

Note 2: High or low state. $I_{\mbox{OUT}}$ absolute maximum rating must be observed.

Note 3: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V	2.0 to 3.6	V	
Fower supply voltage	V _{CC}	1.5 to 3.6 (Note 4)	V	
Input voltage	V _{IN}	0 to 5.5	V	
Output voltage	Vour	0 to 5.5 (Note 5)	V	
Output voltage	Vout	0 to V _{CC} (Note 6)	V	
Output current	I _{OH} /I _{OL}	±12 (Note 8)	mA	
		±8 (Note 9)		
Operating temperature	T _{opr}	-40 to 85	°C	
Input rise and fall time	dt/dv	0 to 10 (Note 10)	ns/V	

Note 4: Data retention only

Note 5: Output in OFF state

Note 6: High or low state

Note 7: $V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$

Note 8: $V_{CC} = 2.7 \text{ to } 3.0 \text{ V}$

Note 9: $V_{CC} = 2.3 \text{ to } 2.7 \text{ V}$

Note 10: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V



Electrical Characteristics

DC Characteristics ($Ta = -40 \text{ to } 85^{\circ}\text{C}$)

Characteristics Symbol T		Test Co	ondition		Min	Max	Unit						
Onaracteristi		Cyrribor	rest condition		V _{CC} (V)	IVIIII	IVIAX	Offic					
	H-level	\/				1.7	_						
Input voltage	i i-levei	V _{IH}			2.7 to 3.6	2.0	_	V					
input voltage	L-level	V _{IL}			2.3 to 2.7	_	0.7	V					
	L-level	۷IL			2.7 to 3.6	_	0.8						
				I _{OH} = -100 μA	2.3 to 3.6	V _{CC} -0.2							
				$I_{OH} = -8 \text{ mA}$	2.3	1.8	_						
	H-level	V _{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -12 \text{ mA}$	2.7	2.2	_						
				$I_{OH} = -18 \text{ mA}$	$I_{OH} = -18 \text{ mA}$	3.0	2.4	_					
Output voltage				$I_{OH} = -24 \text{ mA}$	3.0	2.2	_	V					
				$I_{OL} = 100 \mu A$	2.3 to 3.6	_	0.2						
								$I_{OL} = 8 \text{ mA}$	I _{OL} = 8 mA	2.3	_	0.6	
	L-level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH} \ or \ V_{IL}$	I _{OL} = 12 mA	2.7	_	0.4					
					I _{OL} = 16 mA	3.0	_	0.4					
				I _{OL} = 24 mA	3.0	_	0.55						
Input leakage current		I _{IN}	$V_{IN} = 0$ to 5.5 V		2.3 to 3.6	_	±5.0	μΑ					
3-state output OFF sta	te current	lo-	$V_{IN} = V_{IH}$ or V_{IL}		2.3 to 3.6	_	±5.0						
3-state output OFF state current		l _{OZ}	V _{OUT} = 0 to 5.5 V		2.3 10 3.0		±3.0	μА					
Power-off leakage curr	ent	I _{OFF}	$V_{IN}/V_{OUT} = 5.5 \text{ V}$		0	_	10.0	μΑ					
Quiescent supply curre	ant	loo	$V_{IN} = V_{CC}$ or GND		2.3 to 3.6	_	20.0						
Quiescent supply cure	71 IL	Icc	V _{IN} /V _{OUT} = 3.6 to 5.5 V		2.3 to 3.6	_	±20.0	μΑ					
Increase in Icc per inpu	ut	Δlcc	$V_{IH} = V_{CC} - 0.6 V$		2.3 to 3.6	_	500						

AC Characteristics ($Ta = -40 \text{ to } 85^{\circ}\text{C}$)

Characteristics	Symbol	Test Condition			Min	Max	Unit					
Characteristics	Symbol	rest Condition	V _{CC} (V)	CL(pF)	IVIIII	IVIAX	Offic					
	+		2.5 ± 0.2	30	1.5	5.4						
Propagation delay time	t _{pLH}	Figure 1, Figure 2	2.7	50	1.5	5.3	ns					
	^t pHL		3.3 ± 0.3	50	1.5	4.5						
	t _{pZL}			2.5 ± 0.2	30	1.5	7.0					
3-state output enable time		Figure 1, Figure 3	2.7	50	1.5	6.0	ns					
	чр∠Н	^t pZH		50	1.5	5.4						
	t _{pLZ}			2.5 ± 0.2	30	1.5	6.4					
3-state output disable time							Figure 1, Figure 3	2.7	50	1.5	5.4	ns
							чрНZ	чрHZ	чрНZ	чрНZ	чрНZ	
			2.5 ± 0.2	30								
Output to output skew	tosLH	(Note 11)	2.7	50			ns					
	t _{osHL}	₹osHL		3.3 ± 0.3	50	_	1.0					

Note 11: Parameter guaranteed by design. $(t_{OSLH} = |t_{DLHm} - t_{DLHn}|, \, t_{OSHL} = |t_{DHLm} - t_{DHLn}|)$

Dynamic Switching Characteristics (Ta = 25°C, input: $t_r = t_f = 2.5$ ns, $R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Тур.	Unit
Quiet output maximum	V _{OLP}	V _{IH} = 2.5 V, V _{IL} = 0 V, C _L =30pF	2.5	0.6	V
dynamic V _{OL}	VOLP	$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}, C_L = 50 \text{pF}$	3.3	0.8	,
Quiet output minimum	V _{OLV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}, C_L = 30 \text{pF}$	2.5	0.6	V
dynamic V _{OL}	I V OLVI	V _{IH} = 3.3 V, V _{IL} = 0 V, C _L =50pF	3.3	0.8	٧

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition		V _{CC} (V)	Тур.	Unit
Input capacitance	C _{IN}	_		3.3	7	pF
Output capacitance	C _{OUT}	_		3.3	8	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz	(Note 12)	3.3	25	pF

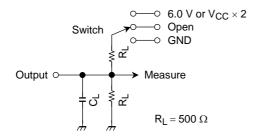
Note 12: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

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Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16 \text{ (per bit)}$

AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}			
t _{pHZ} , t _{pZH}	GND		

Figure 1

AC Waveform

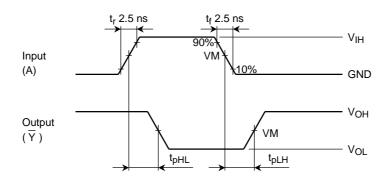


Figure 2 t_{pLH}, t_{pHL}

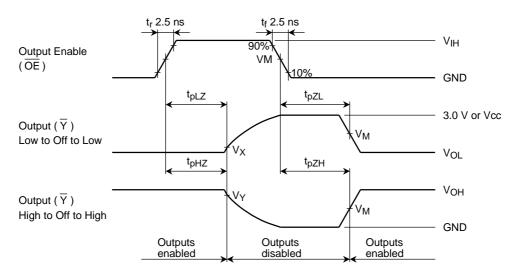
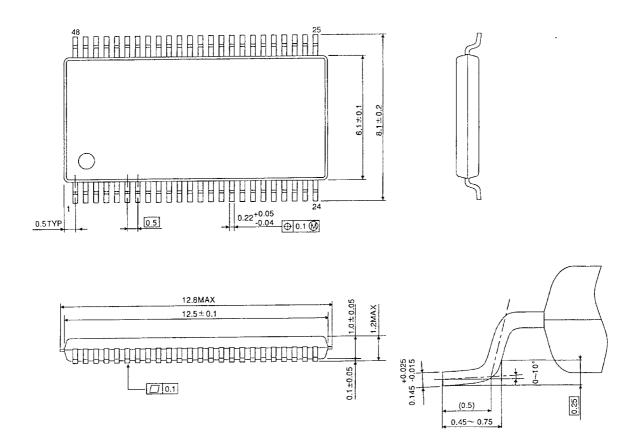


Figure 3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol		V _{CC}	
Symbol	$3.3\pm0.3~\textrm{V}$	2.7 V	$2.5\pm0.2\textrm{V}$
V_{IH}	2.7 V	2.7 V	Vcc
V _M	1.5 V	1.5 V	V _{CC} /2
VX	V _{OL} + 0.3 V	V _{OL} + 0.3 V	V _{OL} + 0.15 V
VY	V _{OH} – 0.3 V	V _{OH} – 0.3 V	V _{OH} – 0.15 V

Package Dimensions

TSSOP48-P-0061-0.50 Unit: mm



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Weight: 0.25 g (typ.)

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